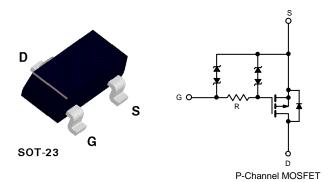
# P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)		
	0.018 at V <sub>GS</sub> = - 4.5 V	- 6 <sup>a</sup>			
- 20	$0.026$ at $V_{GS} = -2.5 \text{ V}$	- 6 <sup>a</sup>	20 nC		
	0.065 at V <sub>GS</sub> = - 1.8 V	- 4			



#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R<sub>g</sub> Tested Built in ESD Protection with Zener Diode
- Typical ESD Performance: 1800 V
- Compliant to RoHS Directive 2002/95/EC

HALOGEN **FREE** 

#### **APPLICATIONS**

- Portable Devices
  - Load Switch
  - Battery Switch
  - Charger Switch

Parameter		Symbol Limit		Unit	
Drain-Source Voltage	V <sub>DS</sub>	- 20	V		
Gate-Source Voltage		$V_{GS}$	± 12	V	
Continuous Drain Current (T <sub>.1</sub> = 150 °C)	$T_C = 25 \degree C$ $T_C = 70 \degree C$	I <sub>D</sub>	- 6 <sup>a</sup> - 6 <sup>a</sup>		
	$T_A = 25 ^{\circ}\text{C}$ $T_A = 70 ^{\circ}\text{C}$		- 5 <sup>b, c</sup> - 4.1 <sup>b, c</sup>	A	
Pulsed Drain Current		I <sub>DM</sub>	- 50		
Continuous Source-Drain Diode Current	$T_C = 25 ^{\circ}C$ $T_A = 25 ^{\circ}C$	I <sub>S</sub>	- 6 <sup>a</sup> - 2.9 <sup>b, c</sup>		
Maximum Power Dissipation	$T_C = 25 ^{\circ}\text{C}$ $T_C = 70 ^{\circ}\text{C}$	D	19 12	W	
Maximum Power Dissipation	$T_A = 25  ^{\circ}\text{C}$ $T_A = 70  ^{\circ}\text{C}$	P <sub>D</sub>	3.5 <sup>b, c</sup> 2.2 <sup>b, c</sup>		
Operating Junction and Storage Temperature Ra	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C		
Soldering Recommendations (Peak Temperature	Ŭ	260			

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>b, e</sup>	t ≤ 5 s	R <sub>thJA</sub>	28	36	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	5.3	6.5	] 5/ ۷۷	

- a. Package limited.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- e. Maximum under Steady State conditions is 80 °C/W.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 20			V	
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I <sub>D</sub> = - 250 μA		- 12		>//00	
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	1D = - 230 μΑ		3		mV/°C	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	- 0.5		- 1.2	V	
Cata Sauraa Laakaga	lass	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 20		
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 0.5	μA	
Zero Gate Voltage Drain Current	lace	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$			- 1		
Zero Gate voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$			- 10	1	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le$ - 5 V, $V_{GS}$ = - 4.5 V	- 20			Α	
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 5.6 A		0.015	0.018		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 5.3 A		0.021	0.026	Ω	
		$V_{GS} = -1.8 \text{ V}, I_D = -2.5 \text{ A}$		0.040	0.065	1	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 5.6 A		35		S	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_g$	V <sub>DS</sub> = - 10 V, V <sub>GS</sub> = - 8 V, I <sub>D</sub> = - 5 A		50	75		
Gate-Source Charge				20	30	nC	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -5 \text{ A}$		3.3			
Gate-Drain Charge	$Q_{gd}$			8.4			
Gate Resistance	$R_g$	f = 1 MHz	0.2	1	2	kΩ	
Turn-On Delay Time	t <sub>d(on)</sub>			0.71	1.1		
Rise Time	t <sub>r</sub>	$V_{DD} = -10 \text{ V}, R_L = 1 \Omega$		1.7	2.6		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong -5 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1$		6	9	us	
Fall Time	t <sub>f</sub>	Ω		3.2	5		
Turn-On Delay Time	t <sub>d(on)</sub>			0.3	0.45	us	
Rise Time	t <sub>r</sub>	$V_{DD} = -10 \text{ V}, R_L = 1 \Omega$		0.6	0.9		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong -5 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1$		10	15		
Fall Time	t <sub>f</sub>	Ω		3.5	5.5		
<b>Drain-Source Body Diode Characterist</b>	ics					1	
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			- 6	Α	
Pulse Diode Forward Current	I <sub>SM</sub>				- 50	, ,	
Body Diode Voltage	$V_{SD}$	$I_S = -5 \text{ A}, V_{GS} = 0 \text{ V}$		- 0.85	- 1.2	V	
Body Diode Reverse Recovery Time	t <sub>rr</sub>			30	60	ns	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> = 6 A, dI/dt = 100 A/μs, T <sub>J</sub> = 25 °C		20	40	nC	
Reverse Recovery Fall Time	t <sub>a</sub>			13		ns	
Reverse Recovery Rise Time	t <sub>b</sub>			17			

#### Notes:

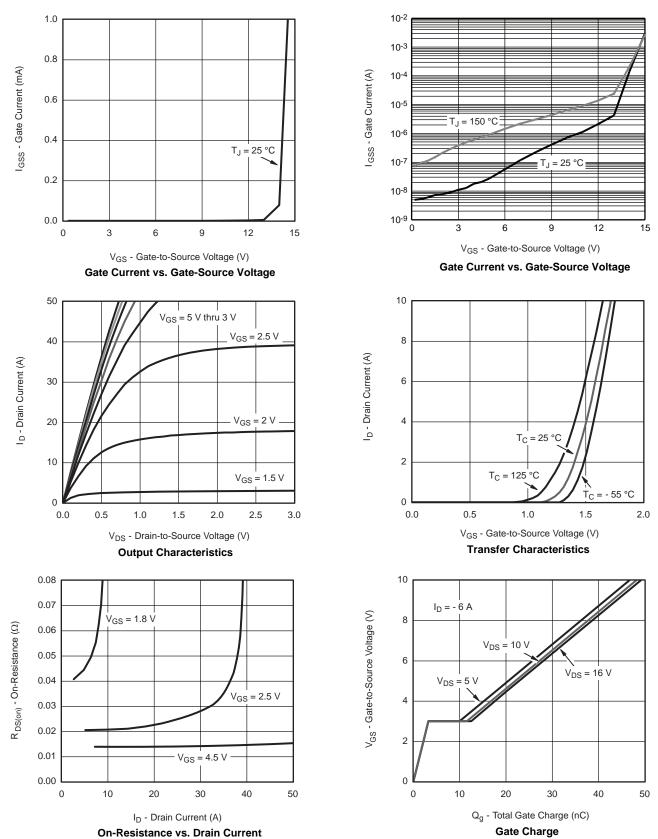
- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$  b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



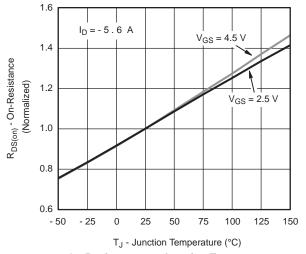


### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

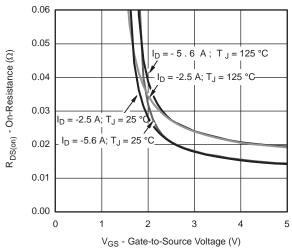




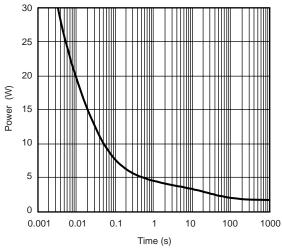
#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



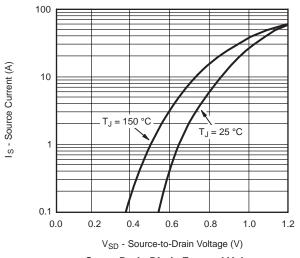
#### On-Resistance vs. Junction Temperature



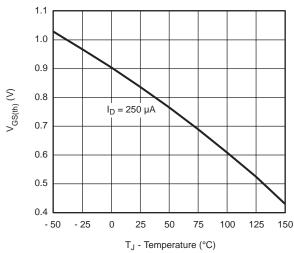
On-Resistance vs. Gate-to-Source Voltage



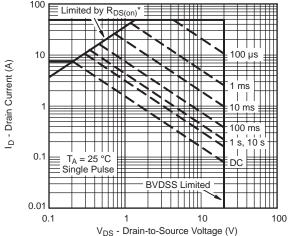
Single Pulse Power, Junction-to-Ambient



#### Soure-Drain Diode Forward Voltage



Threshold Voltage

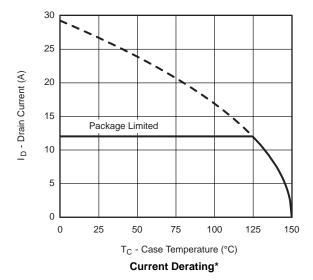


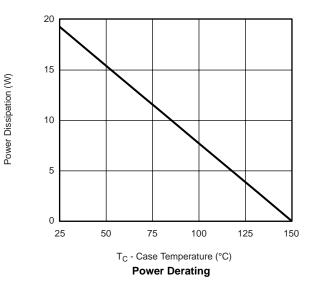
\*  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

Safe Operating Area, Junction-to-Ambient

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## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



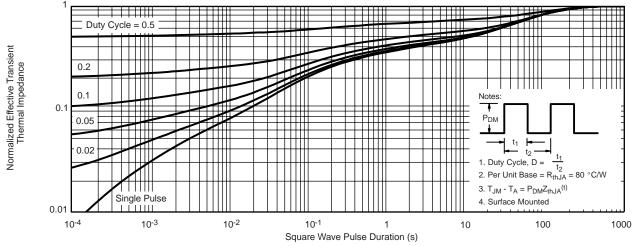


<sup>\*</sup> The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit

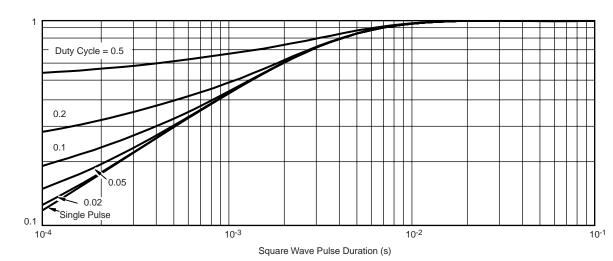


Normalized Effective Transient Thermal Impedance

### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



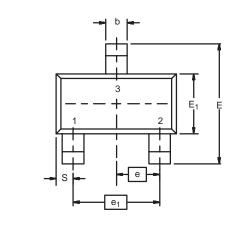
Normalized Thermal Transient Impedance, Junction-to-Ambient

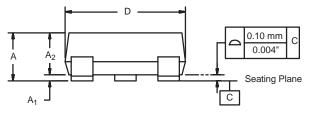


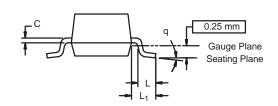
Normalized Thermal Transient Impedance, Junction-to-Case



## SOT-23 (TO-236): 3-LEAD







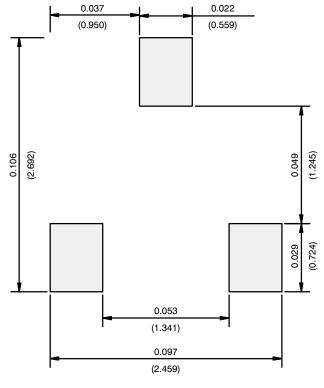
Dim	MILLIMETERS		INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A <sub>1</sub>	0.01	0.10	0.0004	0.004	
A <sub>2</sub>	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E <sub>1</sub>	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e <sub>1</sub>	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L <sub>1</sub>	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	

ECN: S-03946-Rev. K, 09-Jul-01

DWG: 5479



#### **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)

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